

Power Transistor (–100V , –2A)

2SB1580 / 2SB1316

●Features

- 1) Darlington connection for high DC current gain.
- 2) Built-in resistor between base and emitter.
- 3) Built-in damper diode.
- 4) Complements the 2SD2195 / 2SD1980.

●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V _{CB0}	–100	V
Collector-emitter voltage	V _{CE0}	–100	V
Emitter-base voltage	V _{EB0}	–8	V
Collector current	I _C	–2	A(DC)
		–3	A(Pulse) *1
Collector power dissipation	P _C	2	W
		10	W(Tc=25°C) *2
Junction temperature	T _J	150	°C
Storage temperature	T _{stg}	–55~+150	°C

*1 Single pulse P_W=100ms

*2 When mounted on a 40 x 40 x 0.7 mm ceramic board.

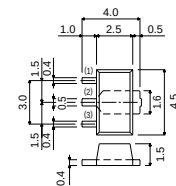
●Packaging specifications and h_{FE}

Type	2SB1580	2SB1316
Package	MPT3	CPT3
h _{FE}	1k~10k	1k~10k
Marking	BN*	–
Code	T100	TL
Basic ordering unit (pieces)	1000	2500

* Denotes h_{FE}

●External dimensions (Units : mm)

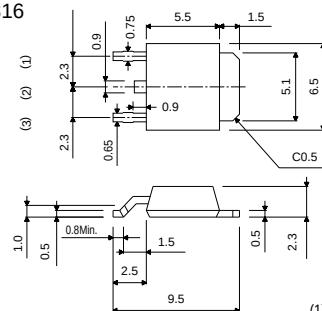
2SB1580



ROHM : MPT3
EIAJ : SC-62

(1) Base(Gate)
(2) Collector(Drain)
(3) Emitter(Source)

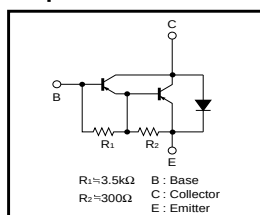
2SB1316



ROHM : CPT3
EIAJ : SC-63

(1) Base(Gate)
(2) Collector(Drain)
(3) Emitter(Source)

●Equivalent circuit



●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV _{CB0}	–100	–	–	V	I _C = –50μA
Collector-emitter breakdown voltage	BV _{CE0}	–100	–	–	V	I _C = –5mA
Collector cutoff current	I _{CBO}	–	–	–10	μA	V _{CB} = –100V
Emitter cutoff current	I _{EB0}	–	–	–3	mA	V _{EB} = –7V
Collector-emitter saturation voltage	V _{CE(sat)}	–	–	–1.5	V	I _C /I _B = –1A/–1mA
DC current transfer ratio	h _{FE}	1000	–	10000	–	V _{CE} = –2V, I _C = –1A
Output capacitance	C _{ob}	–	35	–	pF	V _{CB} = –10V, I _E = 0A, f = 1MHz

* Measured using pulse current.